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[NTGS3433T1G](#)

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# NTGS3433T1

## MOSFET -3.3 Amps, -12 Volts

### P-Channel TSOP-6

#### Features

- Ultra Low  $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- Pb-Free Package is Available

#### Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-12	Volts
Gate-to-Source Voltage - Continuous	$V_{GS}$	$\pm 8.0$	Volts
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_d$	2.0	Watts
Drain Current	$I_D$	-3.3	Amps
- Continuous @ $T_A = 25^\circ\text{C}$	$I_{DM}$	-20	Amps
- Pulsed Drain Current ( $T_p < 10 \mu\text{s}$ )	$P_d$	1.0	Watts
Maximum Operating Power Dissipation	$I_D$	-2.35	Amps
Maximum Operating Drain Current	$I_D$	-2.35	Amps
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	128	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_d$	1.0	Watts
Drain Current	$I_D$	-2.35	Amps
- Continuous @ $T_A = 25^\circ\text{C}$	$I_{DM}$	-14	Amps
- Pulsed Drain Current ( $T_p < 10 \mu\text{s}$ )	$P_d$	0.5	Watts
Maximum Operating Power Dissipation	$I_D$	-1.65	Amps
Maximum Operating Drain Current	$I_D$	-1.65	Amps
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	$T_L$	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

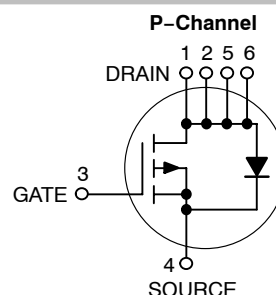
1. Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu 0.06" thick single sided),  $t < 5.0$  seconds.
2. Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu 0.06" thick single sided), operating to steady state.



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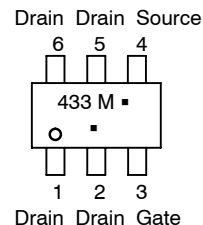
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ Max
-12 V	75 m $\Omega$ @ -4.5 V	-3.3 A



#### MARKING DIAGRAM & PIN ASSIGNMENT



TSOP-6  
CASE 318G  
STYLE 1



433 = Specific Device Code  
 M = Date Code\*  
 ■ = Pb-Free Package

(Note: Microdot may be in either location)  
 \*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
NTGS3433T1	TSOP-6	3000 Tape & Reel
NTGS3433T1G	TSOP-6 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## NTGS3433T1

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Notes 3 & 4)

Characteristic	Symbol	Min	Typ	Max	Unit
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#### OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{ Vdc}$ , $I_D = -10\ \mu\text{A}$ )	$V_{(BR)DSS}$	-12	-	-	Vdc
Zero Gate Voltage Drain Current ( $V_{GS} = 0\text{ Vdc}$ , $V_{DS} = -8\text{ Vdc}$ , $T_J = 25^\circ\text{C}$ ) ( $V_{GS} = 0\text{ Vdc}$ , $V_{DS} = -8\text{ Vdc}$ , $T_J = 70^\circ\text{C}$ )	$I_{DSS}$	-	-	-1.0 -5.0	$\mu\text{A}$
Gate-Body Leakage Current ( $V_{GS} = -8.0\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	-	-	-100	nA
Gate-Body Leakage Current ( $V_{GS} = +8.0\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	-	-	100	nA

#### ON CHARACTERISTICS

Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = -250\ \mu\text{A}$ )	$V_{GS(th)}$	-0.50	-0.70	-1.50	Vdc
Static Drain-Source On-State Resistance ( $V_{GS} = -4.5\text{ Vdc}$ , $I_D = -3.3\text{ A}$ ) ( $V_{GS} = -2.5\text{ Vdc}$ , $I_D = -2.9\text{ A}$ )	$R_{DS(on)}$	-	0.055 0.075	0.075 0.095	$\Omega$
Forward Transconductance ( $V_{DS} = -10\text{ Vdc}$ , $I_D = -3.3\text{ A}$ )	$g_{FS}$	-	7.0	-	mhos

#### DYNAMIC CHARACTERISTICS

Total Gate Charge	$(V_{DS} = -10\text{ Vdc}$ , $V_{GS} = -4.5\text{ Vdc}$ , $I_D = -3.3\text{ A}$ )	$Q_{tot}$	-	7.0	15	nC
Gate-Source Charge		$Q_{gs}$	-	2.0	-	
Gate-Drain Charge		$Q_{gd}$	-	3.5	-	
Input Capacitance	$(V_{DS} = -5.0\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{iss}$	-	550	-	pF
Output Capacitance		$C_{oss}$	-	450	-	
Reverse Transfer Capacitance		$C_{rss}$	-	200	-	

#### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$(V_{DD} = -10\text{ Vdc}$ , $I_D = -1.0\text{ A}$ , $V_{GS} = -4.5\text{ Vdc}$ , $R_g = 6.0\ \Omega$ )	$t_{d(on)}$	-	20	30	ns
Rise Time		$t_r$	-	20	30	
Turn-Off Delay Time		$t_{d(off)}$	-	110	120	
Fall Time		$t_f$	-	100	115	
Reverse Recovery Time	$(I_S = -1.7\text{ A}$ , $dI_S/dt = 100\text{ A}/\mu\text{s}$ )	$t_{rr}$	-	30	-	ns

#### BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage	$(I_S = -1.7\text{ A}$ , $V_{GS} = 0\text{ Vdc}$ )	$V_{SD}$	-	-0.80	-1.5	Vdc
Diode Forward On-Voltage	$(I_S = -3.3\text{ A}$ , $V_{GS} = 0\text{ Vdc}$ )	$V_{SD}$	-	-0.90	-	Vdc

3. Indicates Pulse Test: P.W. = 300  $\mu\text{sec}$  max, Duty Cycle = 2%.

4. Class 1 ESD rated – Handling precautions to protect against electrostatic discharge are mandatory.

### NTGS3433T1

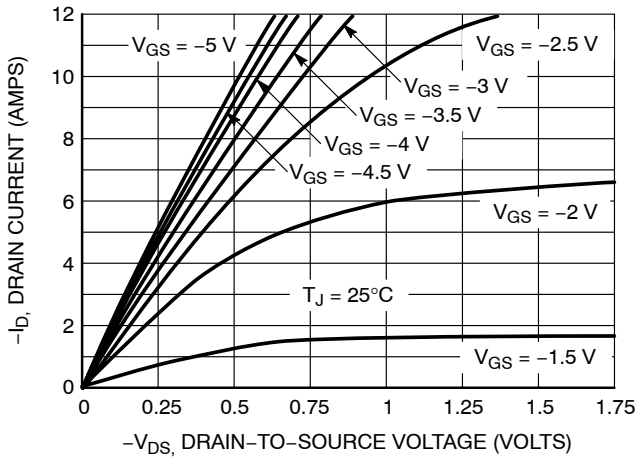


Figure 1. On-Region Characteristics

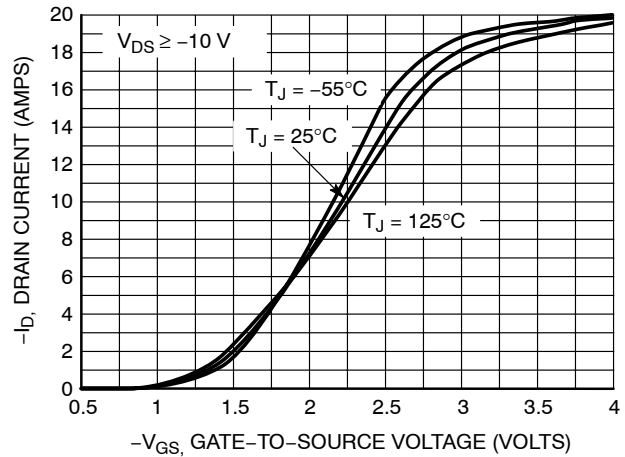


Figure 2. Transfer Characteristics

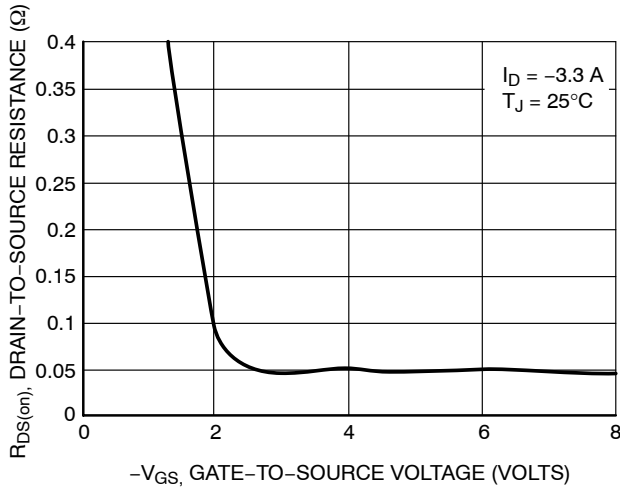


Figure 3. On-Resistance vs. Gate-to-Source Voltage

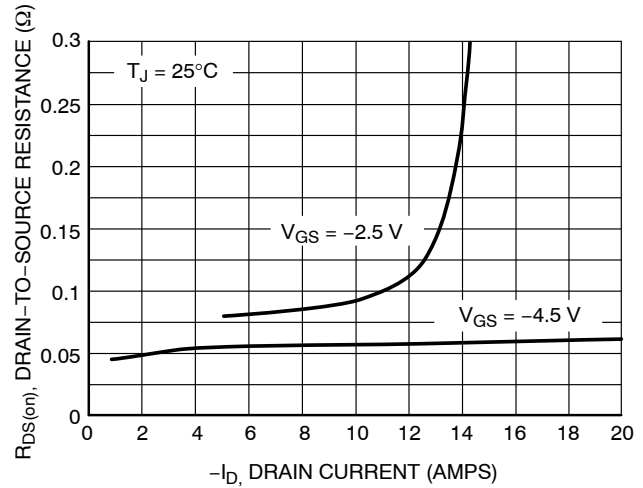


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

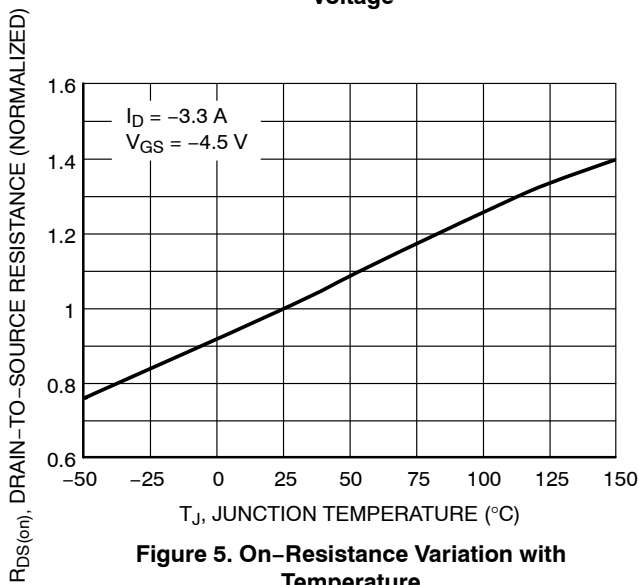


Figure 5. On-Resistance Variation with Temperature

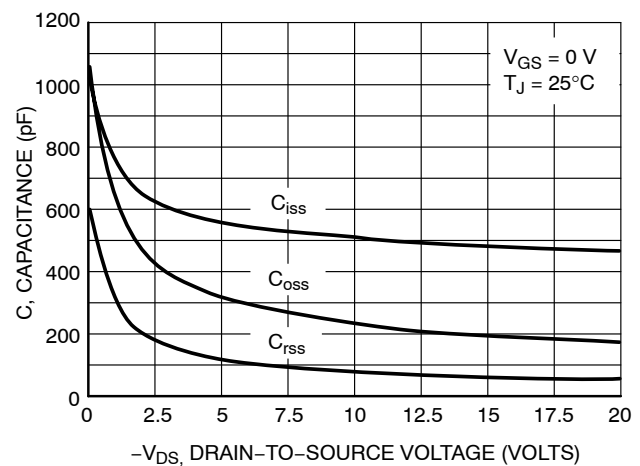
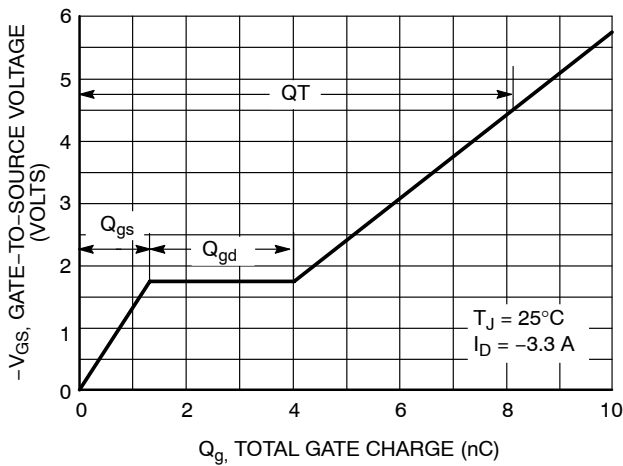
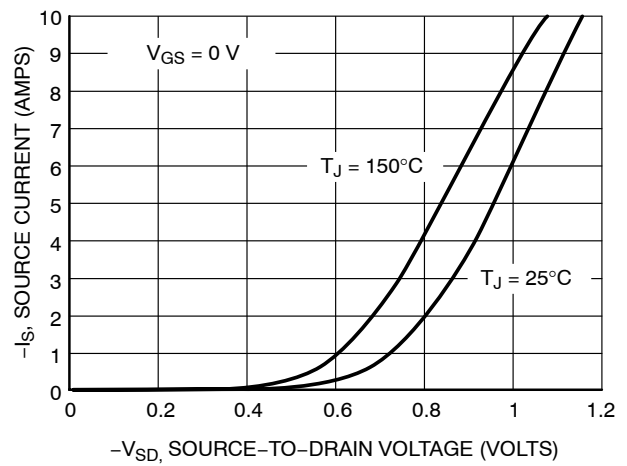


Figure 6. Capacitance Variation

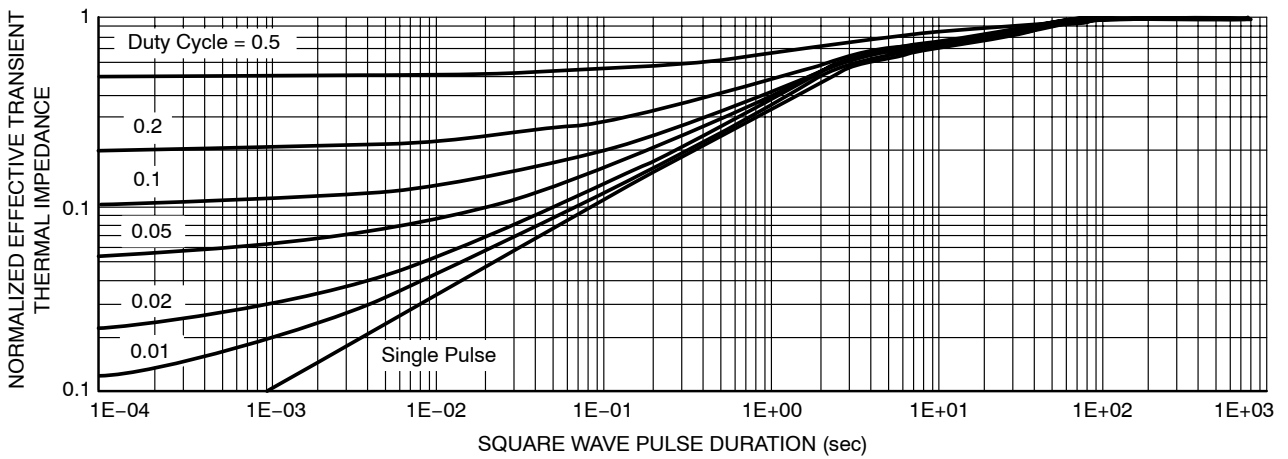
**NTGS3433T1**



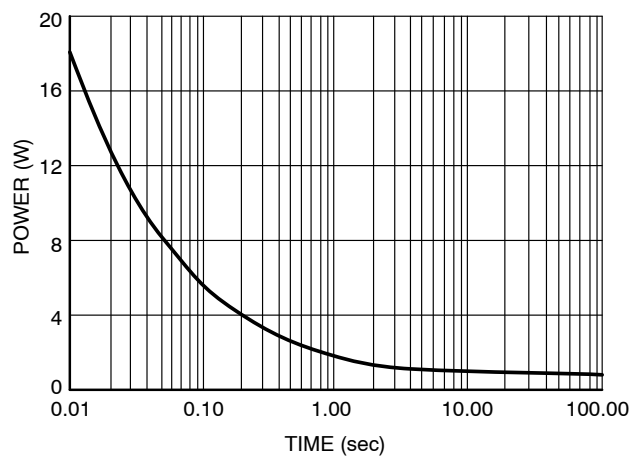
**Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge**



**Figure 8. Diode Forward Voltage vs. Current**



**Figure 9. Normalized Thermal Transient Impedance, Junction-to-Ambient**

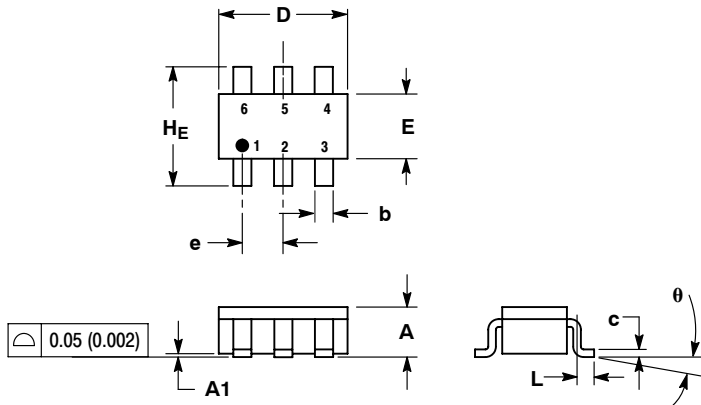


**Figure 10. Single Pulse Power**

## NTGS3433T1

### PACKAGE DIMENSIONS

TSOP-6  
 CASE 318G-02  
 ISSUE P



NOTES:

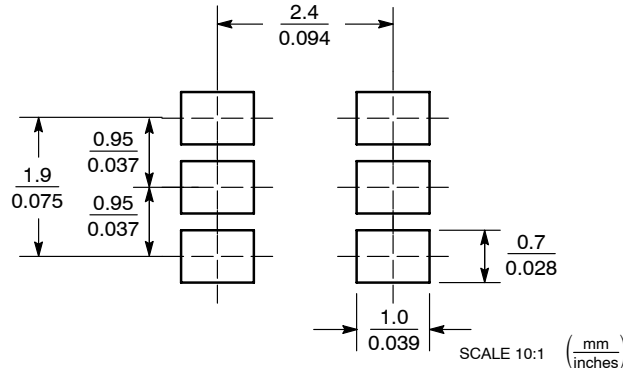
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

STYLE 1:

1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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